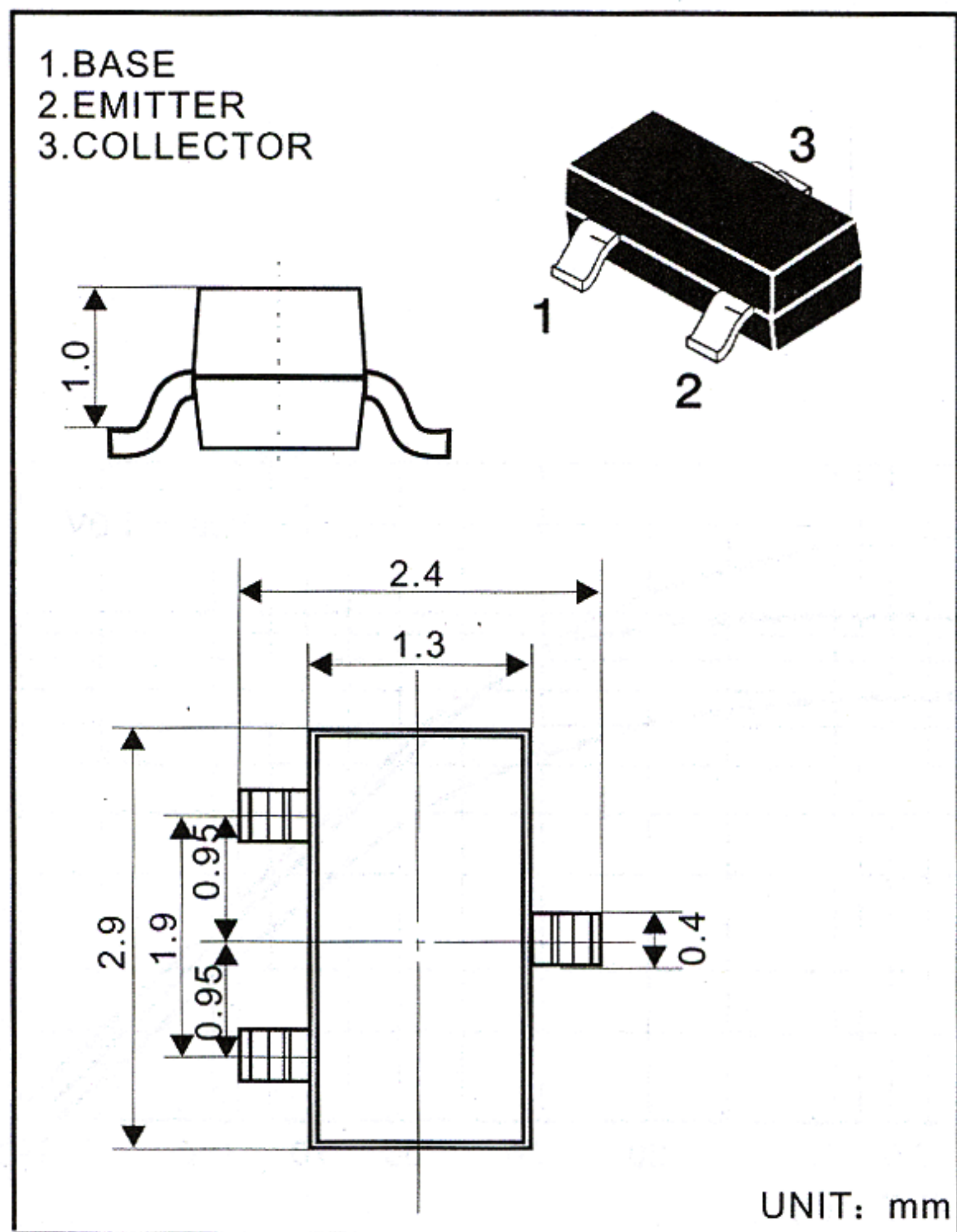


MMBT3906LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.2 A

Collector-base voltage

$V_{(BR)CBO}$: -40V

Operating and storage junction temperature range

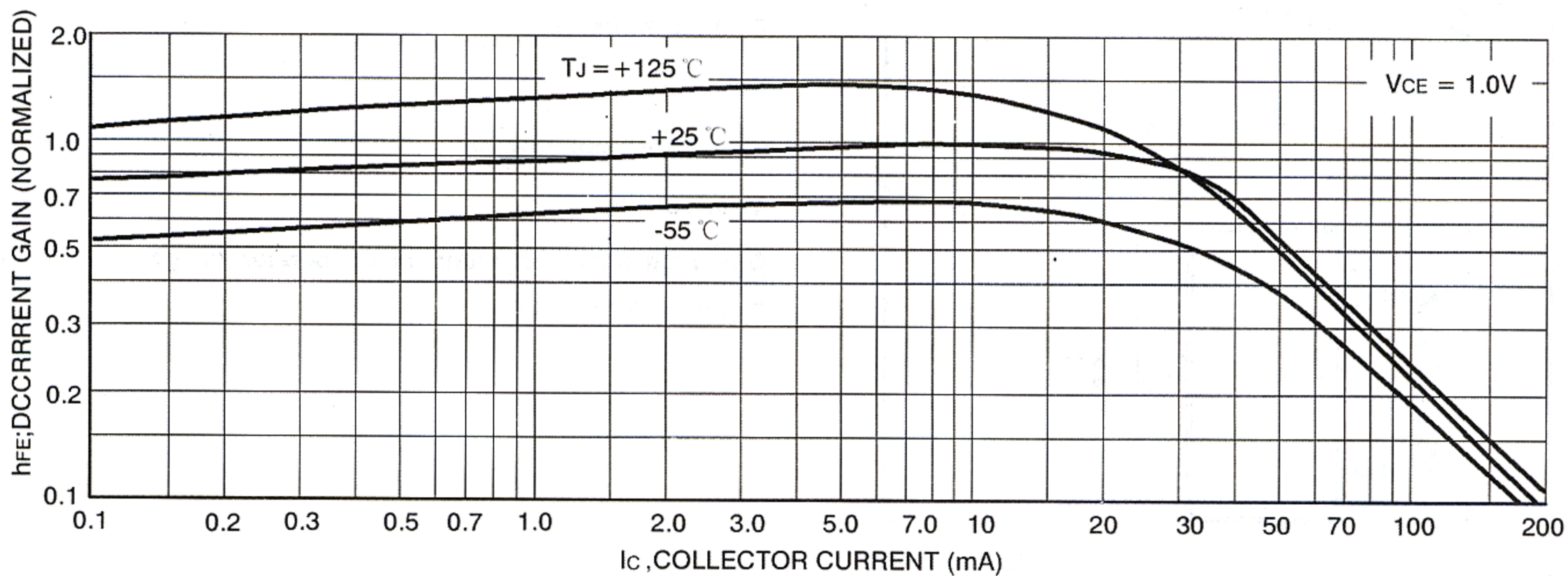
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

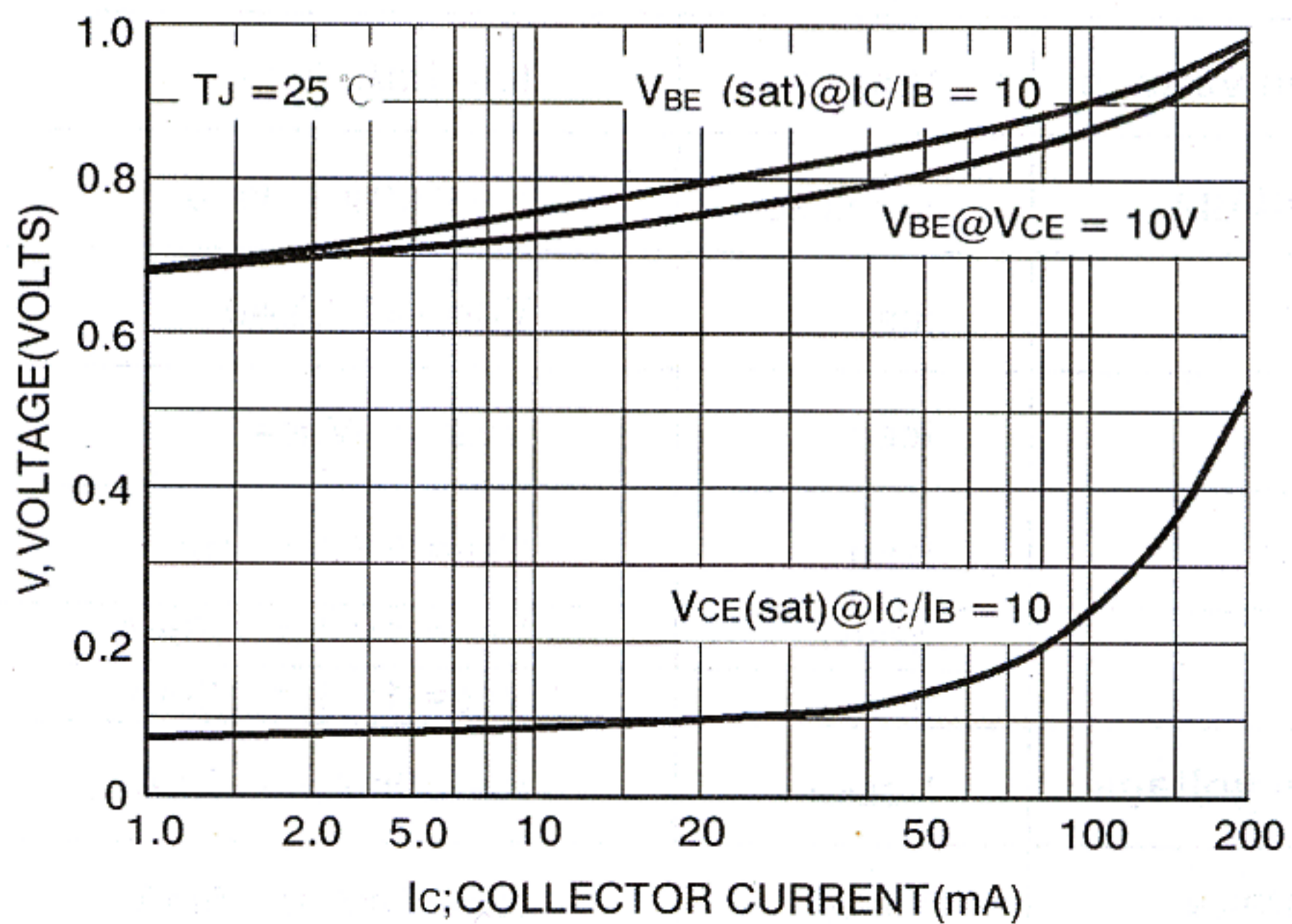
($T_{amp}=25^{\circ}C$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|--------------------------------------|---------------|--|-----|-------|---------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C = -100 \mu A, I_E = 0$ | -40 | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = -1mA, I_B = 0$ | -40 | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_C = -100 \mu A, I_B = 0$ | -5 | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = -40V, I_E = 0$ | | -0.1 | μA |
| Collector cut-off current | I_{CEO} | $V_{CE} = -40V, I_B = 0$ | | -0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -5V, I_C = 0mA$ | | -0.1 | μA |
| DC current gain | $h_{FE(1)}$ | $V_{CE} = -1V, I_C = -10mA$ | 100 | 300 | |
| | $h_{FE(2)}$ | $V_{CE} = -1V, I_C = -50mA$ | 60 | | |
| Collector-emitter saturation voltage | V_{CEsat} | $I_C = -50mA, I_B = -5mA$ | | -0.4 | V |
| Base-emitter saturation voltage | V_{BEsat} | $I_C = -50mA, I_B = -5mA$ | | -0.95 | V |
| Transition frequency | f_T | $V_{CE} = -20V, I_C = -10mA, f = 100MHz$ | 250 | | MHz |

DEVICE MARKING : MMBT3906LT1=2A



DC Current Gain



"On" Voltages